



제 31회 한국반도체학술대회

The 31st Korean Conference on Semiconductors

2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 26일(금), 13:45-15:30

Room F(106), 1층

C. Material Growth & Characterization 분과

[FF2-C] Materials synthesis by design

좌장: 김태헌 교수(울산대학교)

<p>초청발표</p> <p>FF2-C-1</p> <p>13:45-14:15</p>	<p>Study on Oxide Materials with Combinatorial Methods</p> <p>Seunghun Lee</p> <p>Department of Physics, Pukyong National University</p>
<p>FF2-C-2</p> <p>14:15-14:30</p>	<p>Differences in Surface Chemical Behavior and Cleaning Mechanism of Si and SiC</p> <p>Yoonji Ra¹, Juyeol Lee¹, Jin-Goo Park¹, Jooyoung Yang², Tae-Uk Kim², and Tae-Gon Kim¹</p> <p>¹Department of Materials Science and Chemical Engineering, Hanyang University ERICA, ²Cleaning Development Team, SK Siltron Co., Ltd.</p>
<p>FF2-C-3</p> <p>14:30-14:45</p>	<p>Optimization of CVD Growth Conditions for Uniform WS₂ Thin-film Synthesis on a 4-inch Wafer Using a Chloride Precursor</p> <p>Hye Seong Park¹, Ta Gyu Ryu¹, Ha Yeon Choi¹, Hyuk Min Kwon², and Hi Deok Lee¹</p> <p>¹Department of Electronics Engineering, Chungnam National University, ²Semiconductor Convergence Campus of Korea Polytechnics College</p>
<p>초청발표</p> <p>FF2-C-4</p> <p>14:45-15:15</p>	<p>Bottom-up Synthesis of 2D Materials for Future Electronics</p> <p>Seok Joon Yun</p> <p>Department of Semiconductor, University of Ulsan</p>
<p>FF2-C-5</p> <p>15:15-15:30</p>	<p>그래핀/N(질소)-극성 질화갈륨(GaN)의 열화학적 안정성과 원격 에피택시</p> <p>최중훈, 홍영준</p> <p>세종대학교 나노신소재공학과</p>